

CMLD6001DO

**SURFACE MOUNT SILICON
DUAL, ISOLATED, OPPOSING
ULTRA LOW LEAKAGE
SWITCHING DIODE**

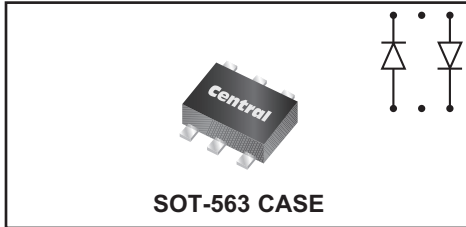


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DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMLD6001DO type contains two (2) isolated opposing configuration, silicon switching diodes, manufactured by the epitaxial planar process, epoxy molded in an SOT-563 surface mount package. These devices are designed for switching applications requiring extremely low leakage.

MARKING CODE: C60



SOT-563 CASE

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

Continuous Reverse Voltage
Peak Repetitive Reverse Voltage
Continuous Forward Current
Peak Forward Surge Current, $t_p=1.0\mu\text{s}$
Peak Forward Surge Current, $t_p=1.0\text{s}$
Power Dissipation
Operating and Storage Junction Temperature
Thermal Resistance

SYMBOL		UNITS
V_R	75	V
V_{RRM}	100	V
I_F	250	mA
I_{FSM}	4.0	A
I_{FSM}	1.0	A
P_D	250	mW
T_J, T_{stg}	-65 to +150	$^\circ\text{C}$
θ_{JA}	500	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS PER DIODE: ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_R	$V_R=75\text{V}$		500	pA
BV_R	$I_R=100\mu\text{A}$	100		V
V_F	$I_F=1.0\text{mA}$		0.85	V
V_F	$I_F=10\text{mA}$		0.95	V
V_F	$I_F=100\text{mA}$		1.1	V
C_J	$V_R=0, f=1.0\text{MHz}$		2.0	pF
t_{rr}	$I_R=I_F=10\text{mA}, I_{rr}=1.0\text{mA}, R_L=100\Omega$		3.0	μs

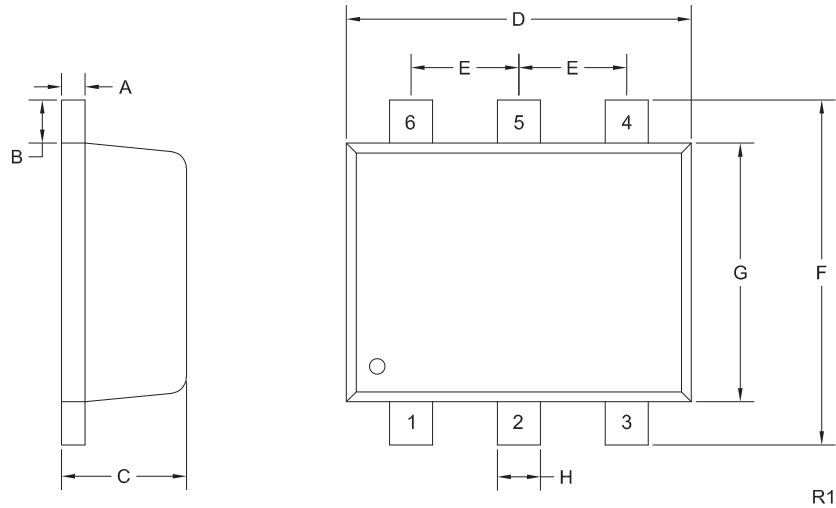
R4 (3-February 2014)

CMLD6001DO

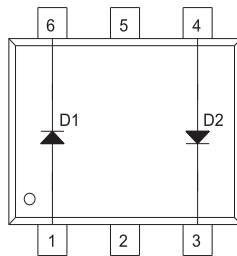
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SOT-563 CASE - MECHANICAL OUTLINE



PIN CONFIGURATION



LEAD CODE:

- 1) Anode D1
- 2) NC
- 3) Cathode D2
- 4) Anode D2
- 5) NC
- 6) Cathode D1

MARKING CODE: C60

DIMENSIONS

SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.0027	0.007	0.07	0.18
B	0.008		0.20	
C	0.017	0.024	0.45	0.60
D	0.059	0.067	1.50	1.70
E	0.020		0.50	
F	0.061	0.067	1.55	1.70
G	0.045	0.049	1.15	1.25
H	0.006	0.012	0.15	0.30

SOT-563 (REV: R1)

R4 (3-February 2014)